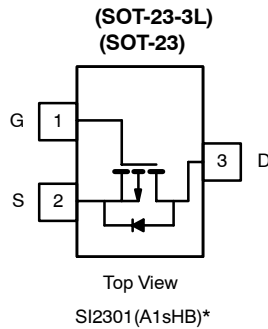




## P-Channel TF2301MOSFET

<b>PRODUCT SUMMARY</b>		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-20	0.120 @ $V_{GS} = -4.5$ V	-2.8
	0.190 @ $V_{GS} = -2.5$ V	-1.8



<b>ABSOLUTE MAXIMUM RATINGS (<math>T_A = 25^\circ\text{C}</math> UNLESS OTHERWISE NOTED)</b>				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	-20	V
Gate-Source Voltage		$V_{GS}$	$\pm 8$	
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>b</sup>	$T_A = 25^\circ\text{C}$	$I_D$	-2.8	A
Pulsed Drain Current <sup>a</sup>		$I_{DM}$	-10	
Continuous Source Current (Diode Conduction) <sup>b</sup>		$I_S$	-1.6	
Power Dissipation <sup>b</sup>	$T_A = 25^\circ\text{C}$	$P_D$	1.25	W
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

<b>THERMAL RESISTANCE RATINGS</b>			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	100	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>c</sup>		166	

Notes

- a. Pulse width limited by maximum junction temperature.
- b. Surface Mounted on FR4 Board,  $t \leq 5$  sec.
- c. Surface Mounted on FR4 Board.



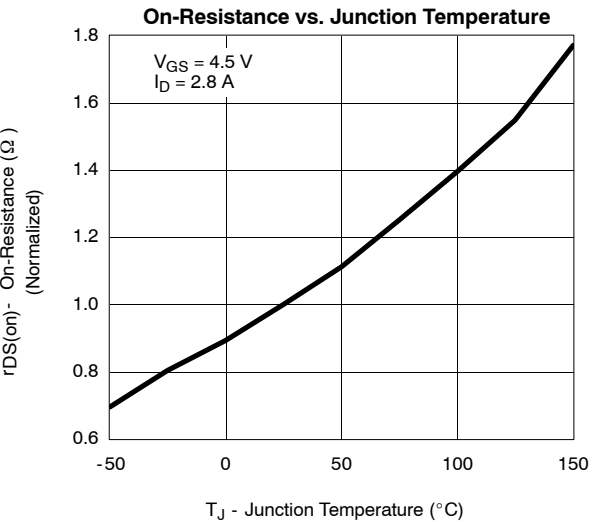
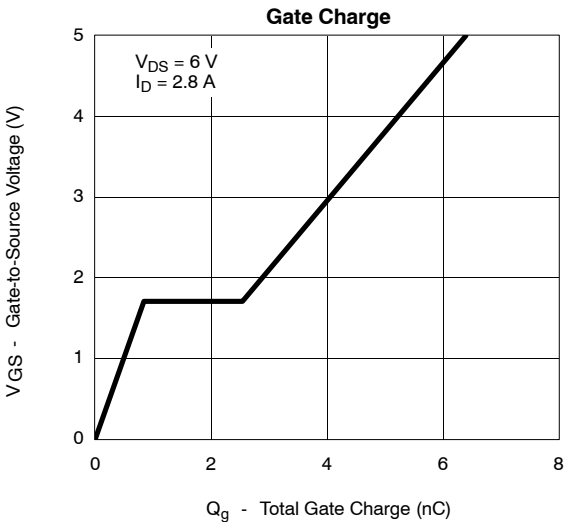
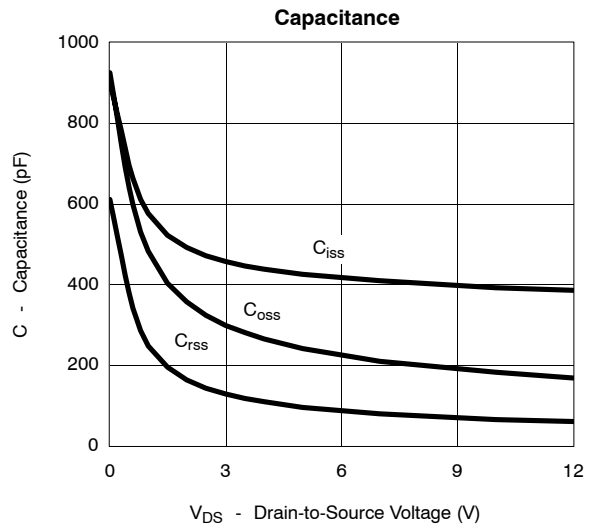
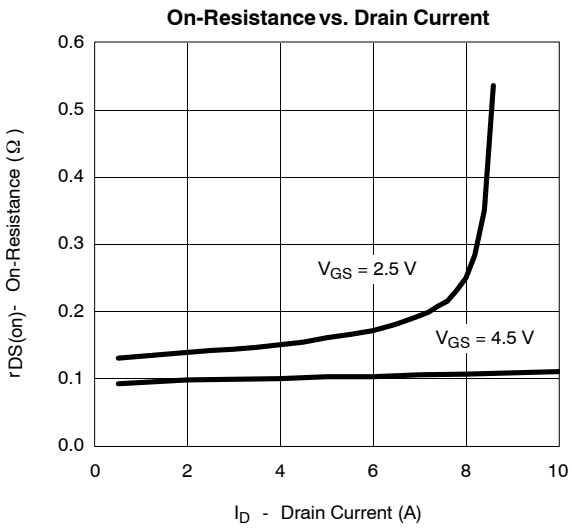
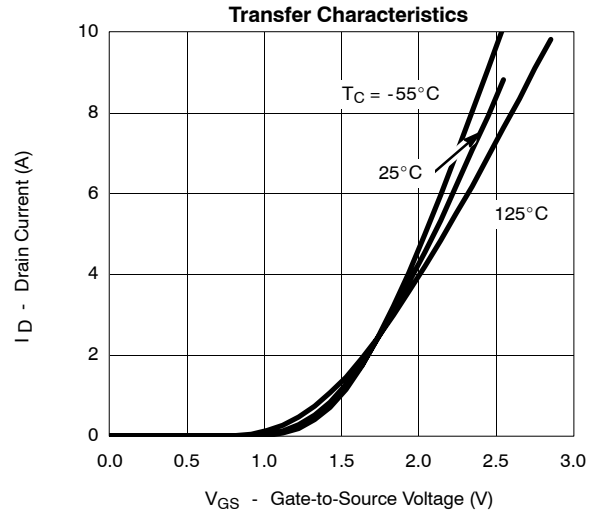
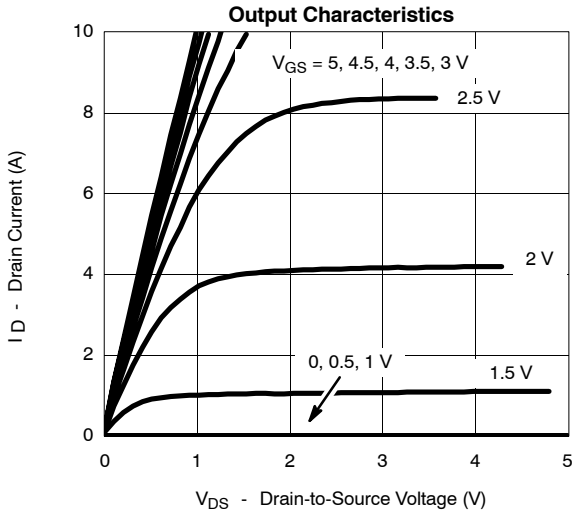
**TF2301**

<b>SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)</b>						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.5		-1.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V			-50	nA
		V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C				
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -4.5 V	-6			A
		V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -2.5 V	-3			
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -2.8 A		0.105	0.120	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -1.8 A		0.145	0.190	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -2.3 A		6.5		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1.6 A, V <sub>GS</sub> = 0 V		-0.80	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -6 V, V <sub>GS</sub> = -4.5 V I <sub>D</sub> ≅ -2.3 A		5.8	10	nC
Gate-Source Charge	Q <sub>gs</sub>			0.85		
Gate-Drain Charge	Q <sub>gd</sub>			1.70		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -6 V, V <sub>GS</sub> = 0, f = 1 MHz		415		pF
Output Capacitance	C <sub>oss</sub>			223		
Reverse Transfer Capacitance	C <sub>rss</sub>			87		
<b>Switching<sup>c</sup></b>						
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -6 V, R <sub>L</sub> = 6 Ω I <sub>D</sub> ≅ -1.0 A, V <sub>GEN</sub> = -4.5 V R <sub>G</sub> = 6 Ω		13.0	25	ns
	t <sub>r</sub>			36.0	60	
Turn-Off Time	t <sub>d(off)</sub>			42	70	
	t <sub>f</sub>			34	60	

Notes

- a. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

